

Silicon NPN Power Transistors

2N5804 2N5805

DESCRIPTION

- With TO-3 package
- High breakdown voltage

APPLICATIONS

- Switching regulator
- Inverters
- Solenoid and relay drivers
- Motor controls

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

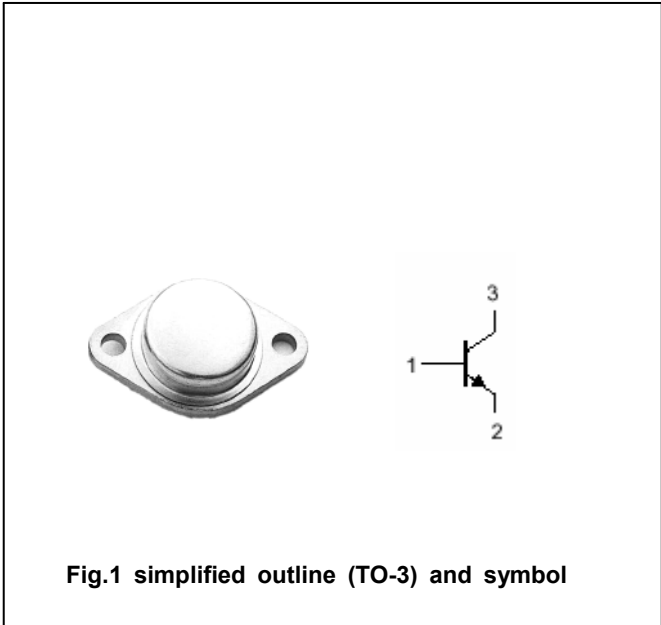


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5804	300	V
		2N5805	375	
V _{CEO}	Collector-emitter voltage	2N5804	225	V
		2N5805	300	
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		5	A
P _D	Total Power Dissipation	T _C =25□	110	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.25	□/W

Silicon NPN Power Transistors

2N5804 2N5805

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5804	I _C =0.1A ; I _B =0	225			V
		2N5805		300			
V _{CEsat}	Collector-emitter saturation voltage		I _C =5A ; I _B =1A			1.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =5A ; I _B =1A			1.5	V
I _{CEO}	Collector cut-off current		V _{CE} =RatedV _{CE} ; I _B =0			10	mA
I _{CEV}	Collector cut-off current	2N5804	V _{CE} =RatedV _{CE} ; V _{BE(off)} =1.5V			12	mA
		2N5805		10			
I _{EBO}	Emitter cut-off current		V _{EB} =7V; I _C =0			1.0	mA
h _{FE}	DC current gain		I _C =5A ; V _{CE} =4V	20		100	
f _T	Transistion frequency		I _C =1A ; V _{CE} =10V	15			MHz

Silicon NPN Power Transistors

2N5804 2N5805

PACKAGE OUTLINE

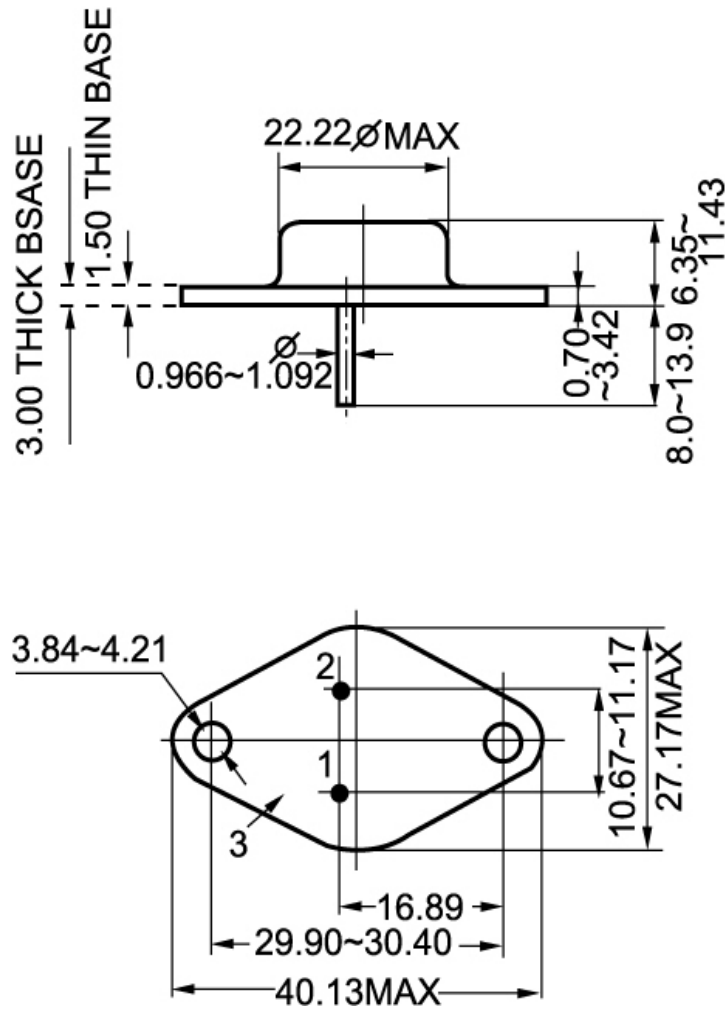


Fig.2 outline dimensions (unindicated tolerance:±0.10mm)